

ISO7142CC-Q1 4242 V_{PK} 小型封装低功耗四通道数字隔离器

1 特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 的下列结果：
 - 器件温度 1 级：-40°C 至 +125°C 的环境运行温度范围
 - 器件人体模型 (HBM) 分类等级 3A
 - 器件充电器件模型 (CDM) 分类等级 C6
- 最大信号传输速率：50Mbps (5V 电源供电)
- 具有集成噪声滤波器的稳健设计
- 低功耗，每通道 I_{CC} 典型值 (3.3V 电源)：
 - 1Mbps 时为 1.3mA，25Mbps 时为 2.5mA
- 典型值为 50kV/μs 的瞬态抗扰度
- 使用 SiO₂ 绝缘隔栅实现长使用寿命
- 可由 2.7V、3.3V 和 5V 电源供电
- 2.7V 和 5V 电平转换
- 小型四分之一尺寸小外形封装 (QSOP)-16 封装
- 安全及管理批准
 - 符合 UL 1577 标准且长达 1 分钟的 2500 V_{RMS} 隔离
 - 符合 DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 标准的 4242 V_{PK} 隔离
 - CSA 组件验收通知 5A, IEC 60950-1 和 IEC 61010-1 终端设备标准
 - 已通过符合 GB4943.1-2011 的 CQC 认证

2 应用

- 通用隔离
- 工业自动化
- 电机控制
- 太阳能逆变器

3 说明

ISO7142CC-Q1 器件可提供符合 UL 1577 标准的长达 1 分钟且高达 2500 V_{RMS} 的电流隔离，以及符合 VDE V 0884-10 标准的 4242 V_{PK} 隔离。

ISO7142CC-Q1 是一款四通道隔离器，此隔离器具有两个正向和两个反向通道。此器件在由 5V 电源供电时的最大数据传输速率为 50Mbps，而在由 3.3V 或 2.7V 电源供电时的最大数据传输速率为 40Mbps。

ISO7142CC-Q1 器件的输入端集成有滤波器，适用于易受噪声干扰的应用。

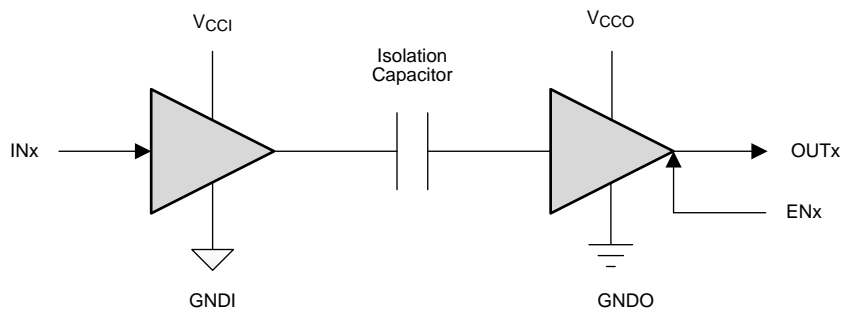
每个隔离通道都有一个由二氧化硅 (SiO₂) 绝缘隔栅分开的逻辑输入和输出缓冲器。与隔离式电源一起使用，这个器件可防止数据总线或者其它电路上的噪音电流进入本地接地和干扰或损坏敏感电路。该器件具有晶体管逻辑电路 (TTL) 输入阈值，并且可由 2.7V、3.3V 和 5V 电压供电运行。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
ISO7142CC-Q1	SSOP (16)	4.90mm × 3.90mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



V_{CCI} 和 GNDI 分别是输入通道的电源和接地连接。

V_{CCO} 和 GNDO 分别是输出通道的电源和接地连接。



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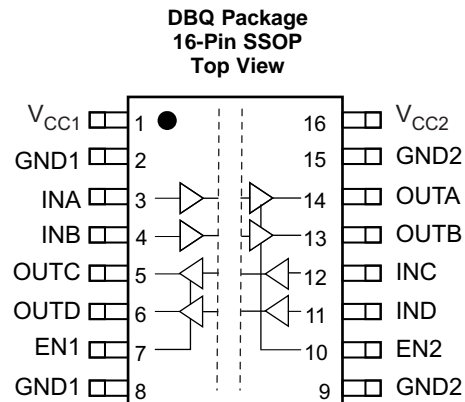
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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

日期	修订版本	注释
2015 年 12 月	*	最初发布。

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN1	7	I	Output enable 1. Output pins on side 1 are enabled when EN1 is high or open and in high-impedance state when EN1 is low.
EN2	10	I	Output enable 2. Output pins on side 2 are enabled when EN2 is high or open and in high-impedance state when EN2 is low.
GND1	2	—	Ground connection for V_{CC1}
	8		
GND2	9	—	Ground connection for V_{CC2}
	15		
INA	3	I	Input, channel A
INB	4	I	Input, channel B
INC	12	I	Input, channel C
IND	11	I	Input, channel D
OUTA	14	O	Output, channel A
OUTB	13	O	Output, channel B
OUTC	5	O	Output, channel C
OUTD	6	O	Output, channel D
V_{CC1}	1	—	Power supply, V_{CC1}
V_{CC2}	16	—	Power supply, V_{CC2}

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage ⁽²⁾	V_{CC1}, V_{CC2}	-0.5	6	V
Voltage	INx, OUTx, ENx	-0.5	$V_{CC} + 0.5^{(3)}$	V
I_O	Output current	-15	15	mA
T_J	Maximum junction temperature		150	°C
T_{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values.
- (3) Maximum voltage must not exceed 6 V.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±4000
		Charged-device model (CDM), per AEC Q100-011	±1500

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V_{CC1}, V_{CC2}	Supply voltage	2.7		5.5	V
I_{OH}	High-level output current	$V_{CC} \geq 3\text{ V}$	-4		mA
		$V_{CC} < 3\text{ V}$	-2		
I_{OL}	Low-level output current			4	mA
V_{IH}	High-level input voltage	2		5.5	V
V_{IL}	Low-level input voltage	0		0.8	V
t_{ui}	Input pulse duration	$V_{CC} \geq 4.5\text{ V}$	20		ns
		$V_{CC} < 4.5\text{ V}$	25		
$1 / t_{ui}$	Signaling rate	$V_{CC} \geq 4.5\text{ V}$	0	50	Mbps
		$V_{CC} < 4.5\text{ V}$	0	40	
T_J	Junction temperature			136	°C
T_A	Ambient temperature	-55	25	125	°C

6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	ISO7142CC-Q1	
		DBQ (SSOP)	UNIT
		16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	104.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	57.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	46.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	18.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	46.4	°C/W
$R_{\theta JCbott}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics—5-V Supply

 V_{CC1} and V_{CC2} at 5 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -4$ mA; see Figure 8	$V_{CCO}^{(1)} - 0.5$			V
		$I_{OH} = -20$ μ A; see Figure 8	$V_{CCO} - 0.1$			
V_{OL}	Low-level output voltage	$I_{OL} = 4$ mA; see Figure 8	0.4			V
		$I_{OL} = 20$ μ A; see Figure 8	0.1			
$V_{I(HYS)}$	Input threshold voltage hysteresis		480			mV
I_{IH}	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx or ENx	10			μ A
I_{IL}	Low-level input current	$V_{IL} = 0$ V at INx or ENx	-10			
CMTI	Common-mode transient immunity	$V_I = V_{CCI}$ or 0 V; see Figure 11	25	70		kV/ μ s

(1) V_{CCI} = Supply voltage for the input channel; V_{CCO} = Supply voltage for the output channel

6.6 Supply Current Characteristics—5-V Supply

 V_{CC1} and V_{CC2} at 5 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current for V_{CC1} and V_{CC2}	Disable	EN1 = EN2 = 0 V	I_{CC1}, I_{CC2}		0.8	1.6	mA
	DC to 1 Mbps	DC signal: $V_I = V_{CCI}$ or 0 V, AC signal: All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		3.3	5	
	10 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		4.9	7	
	25 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		7.3	10	
	50 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		11.1	14.5	

6.7 Electrical Characteristics—3.3-V Supply

 V_{CC1} and V_{CC2} at 3.3 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -4$ mA; see Figure 8	$V_{CCO}^{(1)} - 0.5$			V
		$I_{OH} = -20$ μ A; see Figure 8	$V_{CCO} - 0.1$			
V_{OL}	Low-level output voltage	$I_{OL} = 4$ mA; see Figure 8	0.4			V
		$I_{OL} = 20$ μ A; see Figure 8	0.1			
$V_{I(HYS)}$	Input threshold voltage hysteresis		460			mV
I_{IH}	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx or ENx	10			μ A
I_{IL}	Low-level input current	$V_{IL} = 0$ V at INx or ENx	-10			
CMTI	Common-mode transient immunity	$V_I = V_{CCI}$ or 0 V; see Figure 11	25	50		kV/ μ s

(1) V_{CCI} = Supply voltage for the input channel; V_{CCO} = Supply voltage for the output channel

6.8 Supply Current Characteristics—3.3-V Supply

V_{CC1} and V_{CC2} at 3.3 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current for V_{CC1} and V_{CC2}	Disable	EN1 = EN2 = 0 V	I_{CC1}, I_{CC2}		0.5	1	mA
	DC to 1 Mbps	DC signal: $V_I = V_{CC1}$ or 0 V AC signal: All channels switching with square-wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		2.5	4	
	10 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		3.5	5	
	25 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		5	7	
	40 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		6.5	10	

6.9 Electrical Characteristics—2.7-V Supply

V_{CC1} and V_{CC2} at 2.7 V (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH} High-level output voltage	$I_{OH} = -2$ mA; see Figure 8	$V_{CCO}^{(1)} - 0.3$			V
	$I_{OH} = -20$ μ A; see Figure 8	$V_{CCO} - 0.1$			
V_{OL} Low-level output voltage	$I_{OL} = 4$ mA; see Figure 8	0.4			V
	$I_{OL} = 20$ μ A; see Figure 8	0.1			
$V_{I(HYS)}$ Input threshold voltage hysteresis		360			mV
I_{IH} High-level input current	$V_{IH} = V_{CC1}^{(1)}$ at INx or ENx	10			μ A
I_{IL} Low-level input current	$V_{IL} = 0$ V at INx or ENx	-10			
CMTI Common-mode transient immunity	$V_I = V_{CC1}$ or 0 V; see Figure 11	25	45		kV/ μ s

(1) V_{CCI} = Supply voltage for the input channel; V_{CCO} = Supply voltage for the output channel

6.10 Supply Current Characteristics—2.7-V Supply

V_{CC1} and V_{CC2} at 2.7 V (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS		SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current for V_{CC1} and V_{CC2}	Disable	EN1 = EN2 = 0 V	I_{CC1}, I_{CC2}		0.4	0.8	mA
	DC to 1 Mbps	DC signal: $V_I = V_{CC1}$ or 0 V AC signal: All channels switching with square-wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		2.2	3.5	
	10 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		3	4.2	
	25 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		4.2	5.5	
	40 Mbps	All channels switching with square wave clock input; $C_L = 15$ pF	I_{CC1}, I_{CC2}		5.4	7.5	

6.11 Power Dissipation Characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D Device power dissipation	$V_{CC1} = V_{CC2} = 5.5$ V, $T_J = 150^\circ$ C, $C_L = 15$ pF Input a 25-MHz, 50% duty cycle square wave			170	mW

6.12 Switching Characteristics—5-V Supply

 V_{CC1} and V_{CC2} at 5 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 8	15	21	38	ns
PWD ⁽¹⁾	Pulse width distortion $ t_{PHL} - t_{PLH} $	See Figure 8			3.5	ns
$t_{sk(o)}$ ⁽²⁾	Channel-to-channel output skew time	Same-direction channels			1.5	ns
		Opposite-direction channels			6.5	
$t_{sk(pp)}$ ⁽³⁾	Part-to-part skew time				14	ns
t_r	Output signal rise time	See Figure 8		2.5		ns
t_f	Output signal fall time	See Figure 8		2.1		ns
t_{PHZ} , t_{PLZ}	Disable propagation delay, high/low-to-high impedance output	See Figure 9		7	12	ns
t_{PZH}	Enable propagation delay, high impedance-to-high output	See Figure 9		6	12	ns
t_{PZL}	Enable propagation delay, high impedance-to-low output	See Figure 9		12	23	us
t_{fs}	Fail-safe output delay time from input data or power loss	See Figure 10		8		μ s
t_{GR}	Input glitch rejection time			9.5		ns

(1) Also known as pulse skew

(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals, and loads.

6.13 Switching Characteristics—3.3-V Supply

 V_{CC1} and V_{CC2} at 3.3 V \pm 10% (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 8	16	25	46	ns
PWD ⁽¹⁾	Pulse width distortion $ t_{PHL} - t_{PLH} $	See Figure 8			3	ns
$t_{sk(o)}$ ⁽²⁾	Channel-to-channel output skew time	Same-direction Channels			2	ns
		Opposite-direction Channels			6.5	
$t_{sk(pp)}$ ⁽³⁾	Part-to-part skew time				21	ns
t_r	Output signal rise time	See Figure 8		3		ns
t_f	Output signal fall time	See Figure 8		2.5		ns
t_{PHZ} , t_{PLZ}	Disable propagation delay, from high/low to high-impedance output	See Figure 9		9	14	ns
t_{PZH}	Enable propagation delay, from high-impedance to high output	See Figure 9		9	17	ns
t_{PZL}	Enable propagation delay, from high-impedance to low output	See Figure 9		12	24	us
t_{fs}	Fail-safe output delay time from input data or power loss	See Figure 10		7		μ s
t_{GR}	Input glitch rejection time			11		ns

(1) Also known as pulse skew

(2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.

(3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

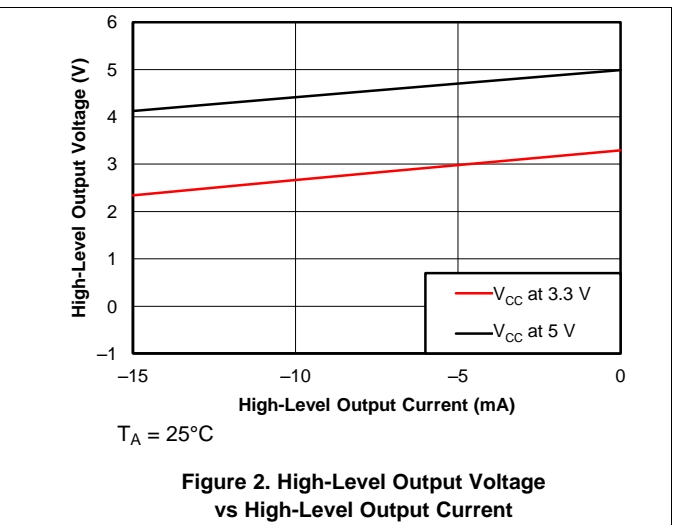
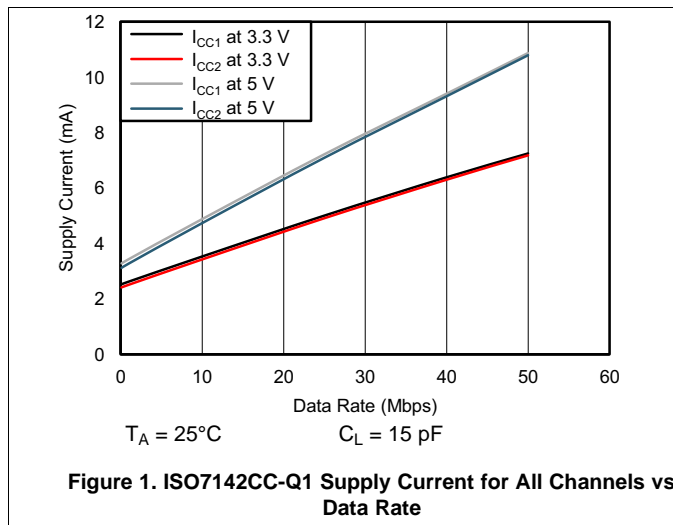
6.14 Switching Characteristics—2.7-V Supply

V_{CC1} and V_{CC2} at 2.7 V (over recommended operating conditions unless otherwise noted.)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 8	18	28	50	ns
PWD ⁽¹⁾	Pulse width distortion $ t_{PHL} - t_{PLH} $	See Figure 8			3	ns
$t_{sk(o)}$ ⁽²⁾	Channel-to-channel output skew time	Same-direction Channels			3	ns
		Opposite-direction Channels			8.5	ns
$t_{sk(pp)}$ ⁽³⁾	Part-to-part skew time				24	ns
t_r	Output signal rise time	See Figure 8		3.5		ns
t_f	Output signal fall time	See Figure 8		2.8		ns
t_{PHZ} , t_{PLZ}	Disable propagation delay, from high/low to high-impedance output	See Figure 9		10	15	ns
t_{PZH}	Enable propagation delay, from high-impedance to high output	See Figure 9		10	19	ns
t_{PZL}	Enable propagation delay, from high-impedance to low output	See Figure 9		12	23	us
t_{fs}	Fail-safe output delay time from input data or power loss	See Figure 10		7		μ s
t_{GR}	Input glitch rejection time			12		ns

- (1) Also known as pulse skew
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals, and loads.

6.15 Typical Characteristics



Typical Characteristics (continued)

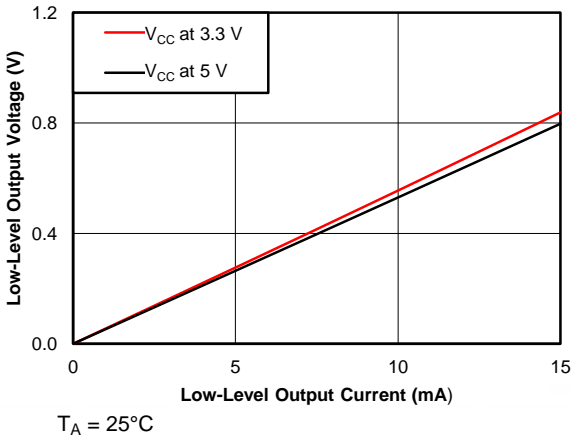


Figure 3. Low-Level Output Voltage vs Low-Level Output Current

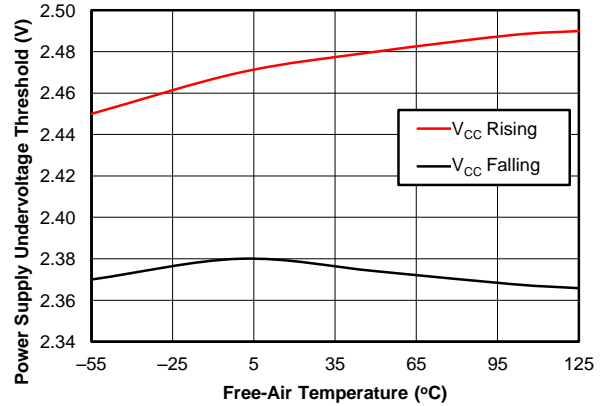


Figure 4. V_{CC} Undervoltage Threshold vs Free-Air Temperature

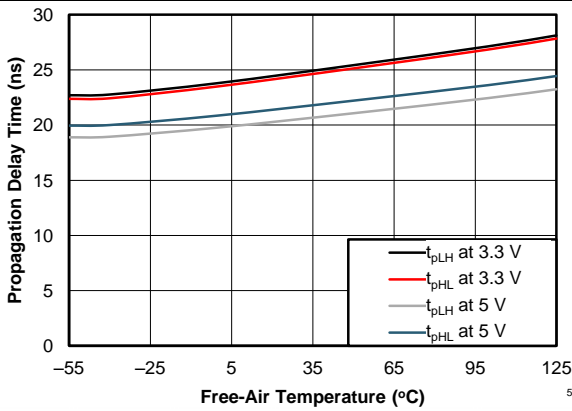


Figure 5. Propagation Delay Time vs Free-Air Temperature

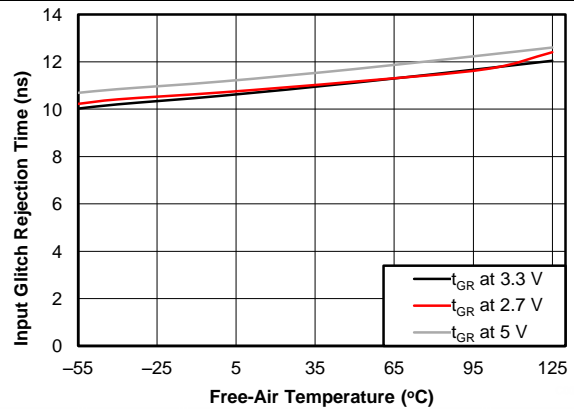


Figure 6. Input Glitch Rejection Time vs Free-Air Temperature

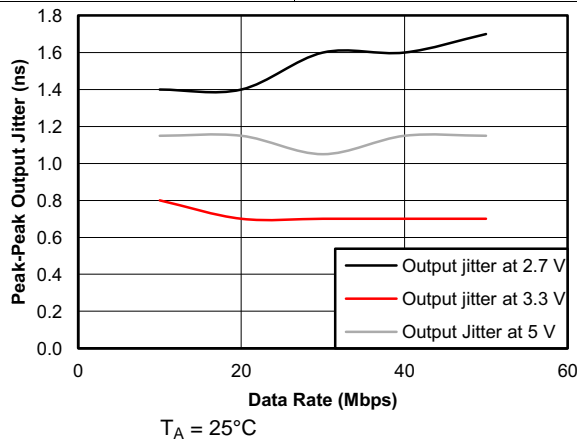
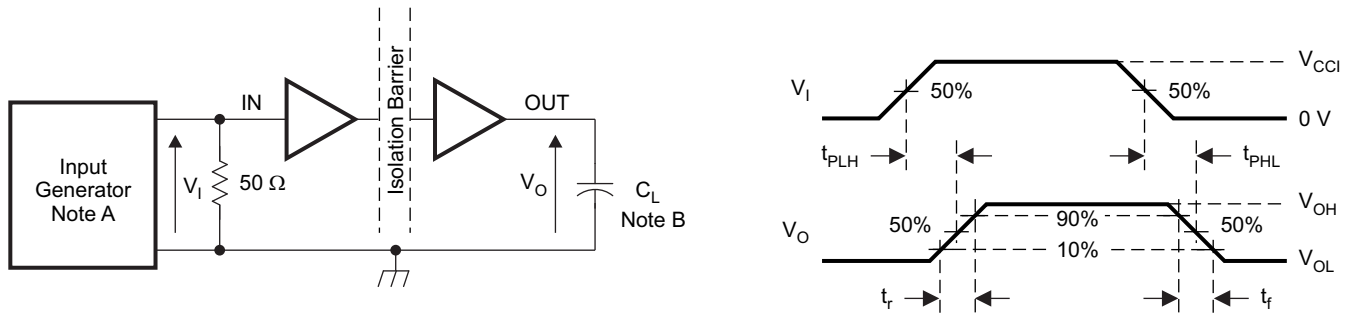


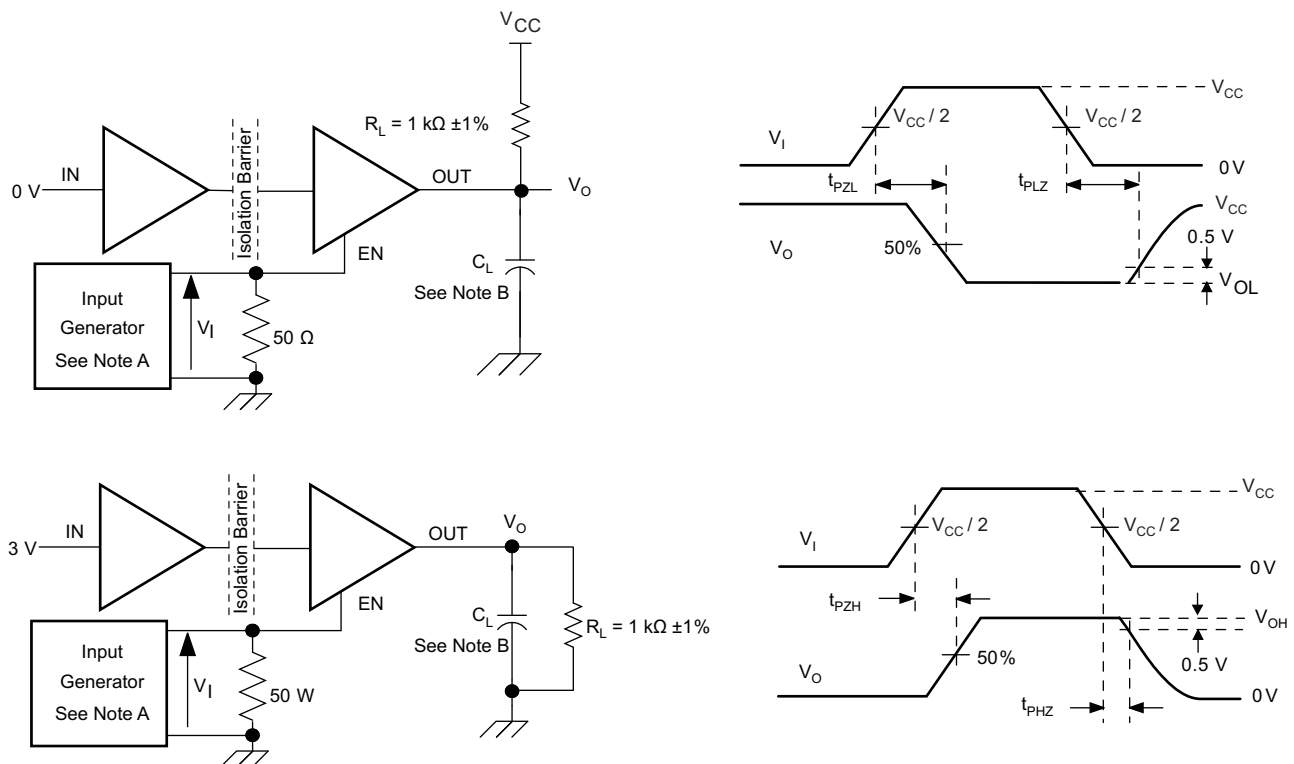
Figure 7. Peak-Peak Output Jitter vs Data Rate

7 Parameter Measurement Information



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_o = 50 \Omega$. At the input, a 50- Ω resistor is required to terminate the input-generator signal. It is not needed in an actual application.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

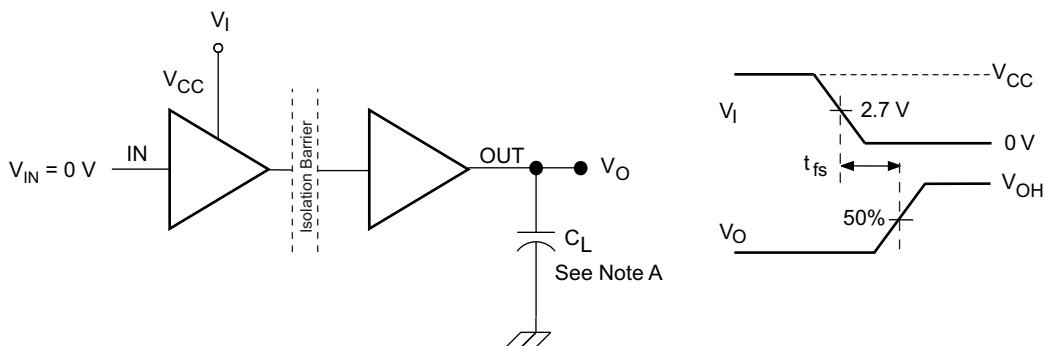
Figure 8. Switching-Characteristics Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_o = 50 \Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

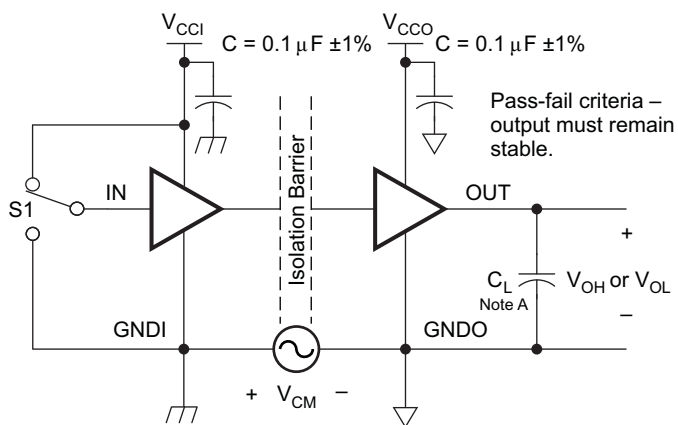
Figure 9. Enable/Disable Propagation Delay-Time Test Circuit and Waveform

Parameter Measurement Information (continued)



A. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 10. Failsafe Delay-Time Test Circuit and Voltage Waveforms



A. $C_L = 15\text{pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 11. Common-Mode Transient Immunity Test Circuit

8 Detailed Description

8.1 Overview

The isolator in [Figure 12](#) is based on a capacitive isolation barrier technique. The I/O channel of the device consists of two internal data channels, a high-frequency channel (HF) with a bandwidth from 100 kbps up to 50 Mbps, and a low-frequency channel (LF) covering the range from 100 kbps down to DC. In principle, a single-ended input signal entering the HF-channel is split into a differential signal through the inverter gate at the input. The following capacitor-resistor networks differentiate the signal into transients, which then are converted into differential pulses by two comparators. The comparator outputs drive a NOR-gate flip-flop whose output feeds an output multiplexer. A decision logic (DCL) at the driving output of the flip-flop measures the durations between signal transients. If the duration between two consecutive transients exceeds a certain time limit, (as in the case of a low-frequency signal), the DCL forces the output-multiplexer to switch from the high- to the low-frequency channel.

Because low-frequency input signals require the internal capacitors to assume prohibitively large values, these signals are pulse-width modulated (PWM) with the carrier frequency of an internal oscillator, thus creating a sufficiently high frequency signal, capable of passing the capacitive barrier. As the input is modulated, a low-pass filter (LPF) is needed to remove the high-frequency carrier from the actual data before passing it on to the output multiplexer.

8.2 Functional Block Diagram

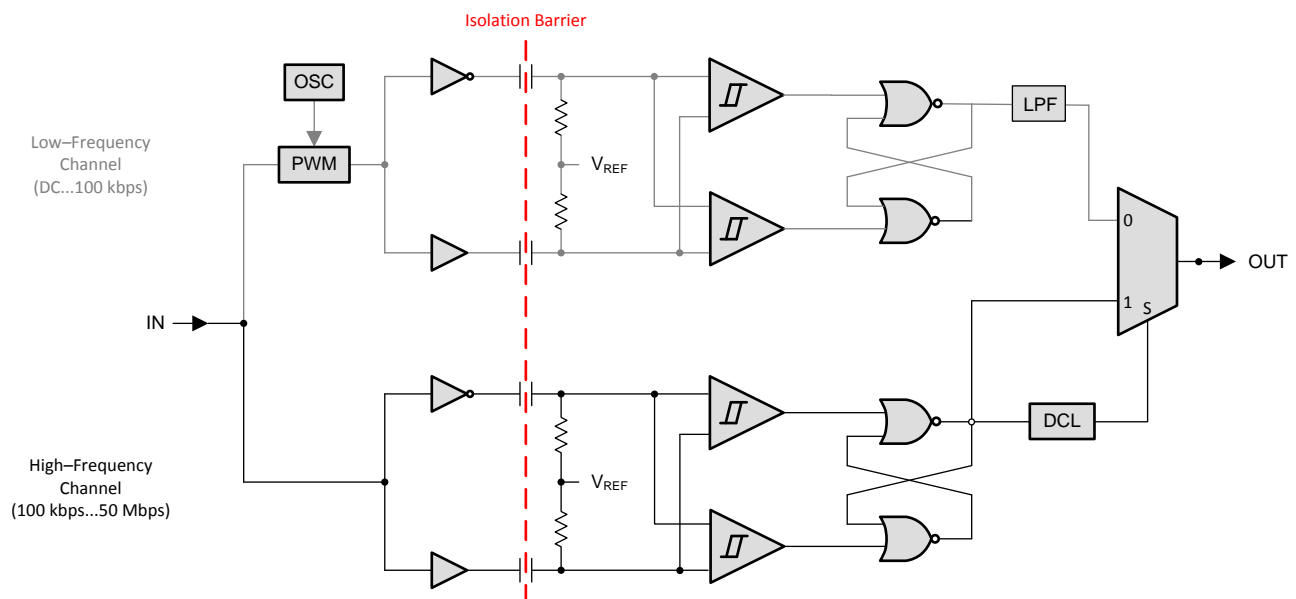


Figure 12. Conceptual Block Diagram of a Digital Capacitive Isolator

8.3 Feature Description

8.3.1 Insulation and Safety-Related Specifications

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	0.014			mm
$C_I^{(1)}$	Input capacitance	$V_I = V_{CC}/2 + 0.4 \sin(2\pi ft)$, $f = 1 \text{ MHz}$, $V_{CC} = 5 \text{ V}$		2		pF
DIN V VDE V 0884-10 (VDE V 0884-10):2006-12						
V_{IOTM}	Maximum transient isolation voltage				4242	V_{PK}
V_{IORM}	Maximum working isolation voltage				566	V_{PK}
V_{PR}	Input-to-output test voltage	After Input/Output safety test subgroup 2/3, $V_{PR} = V_{IORM} \times 1.2$, $t = 10 \text{ s}$, Partial discharge $< 5 \text{ pC}$			679	V_{PK}
		Method a, After environmental tests subgroup 1, $V_{PR} = V_{IORM} \times 1.6$, $t = 10 \text{ s}$, Partial discharge $< 5 \text{ pC}$			906	
		Method b1, 100% production test, $V_{PR} = V_{IORM} \times 1.875$, $t = 1 \text{ s}$, Partial discharge $< 5 \text{ pC}$			1061	
L(101)	Minimum air gap (clearance)	Shortest terminal to terminal distance through air	3.7			mm
L(102)	Minimum external tracking (creepage)	Shortest terminal to terminal distance across the package surface	3.7			mm
CTI	Tracking resistance (comparative tracking index)	DIN EN 60112 (VDE 0303-11); IEC 60112	≥ 400			V
$R_{IO}^{(2)}$	Isolation resistance, input to output	$V_{IO} = 500 \text{ V}$, $T_A = 25^\circ\text{C}$			$>10^{12}$	Ω
		$V_{IO} = 500 \text{ V}$, $100^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$			$>10^{11}$	
		$V_{IO} = 500 \text{ V}$, $T_S = 150^\circ\text{C}$			$>10^9$	
$C_{IO}^{(2)}$	Barrier capacitance, input to output	$V_I = 0.4 \sin(2\pi ft)$, $f = 1 \text{ MHz}$			2.4	pF
UL 1577						
V_{ISO}	Withstanding Isolation voltage	$V_{TEST} = V_{ISO} = 2500 V_{RMS}$, 60 sec (qualification); $V_{TEST} = 1.2 * V_{ISO} = 3000 V_{RMS}$, 1 sec (100% production)			2500	V_{RMS}

(1) Measured from input data pin to ground.

(2) All pins on each side of the barrier tied together creating a two-terminal device.

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance.

Creepage and clearance on a printed circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

Table 1. IEC 60664-1 Ratings Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Material Group		II
Installation classification / Overvoltage Category for Basic Insulation	Rated mains voltage $\leq 150 V_{RMS}$	I–IV
	Rated mains voltage $\leq 300 V_{RMS}$	I–III

8.3.2 Regulatory Information

VDE	UL	CSA	CQC
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 61010-1 (VDE 0411-1):2011-07	Certified under UL 1577 Component Recognition Program	Approved under CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 61010-1	Plan to certify according to GB 4943.1-2011
Basic Insulation; Maximum transient Isolation Isolatiolationvoltage, 4242 V _{PK} Maximum working isolation voltage, 566 V _{PK}	Single protection, 2500 V _{RMS} ⁽¹⁾	3000 V _{RMS} Isolation rating; 185 V _{RMS} Reinforced Insulation and 370 V _{RMS} Basic Insulation per CSA 60950-1-07+A1+A2 and IEC 60950-1 2nd Ed.+A1+A2; 150 V _{RMS} Reinforced Insulation and 300 V _{RMS} Basic Insulation per CSA 61010-1-12 and IEC 61010-1 3rd Ed.	Basic Insulation, Altitude ≤ 5000m, Tropical climate, 250 V _{RMS} maximum working voltage.
File number: 40016131	File number: E181974	Master contract number: 220991	Certification Planned

(1) Production tested ≥ 3000 V_{RMS} for 1 second in accordance with UL 1577.

8.3.3 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S Safety input, output, or supply current	DBQ-16	θ _{JA} = 104.5°C/W, V _I = 5.5 V, T _J = 150°C, T _A = 25°C		217	mA
		θ _{JA} = 104.5°C/W, V _I = 3.6 V, T _J = 150°C, T _A = 25°C		332	
		θ _{JA} = 104.5°C/W, V _I = 2.7 V, T _J = 150°C, T _A = 25°C		443	
T _S Maximum safety temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the [Absolute Maximum Ratings](#) table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

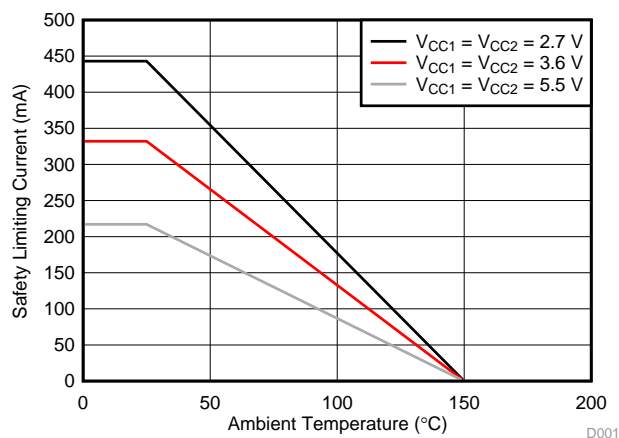


Figure 13. Thermal Derating Curve for Safety Limiting Current per VDE

8.4 Device Functional Modes

Table 2 lists the functional modes for the ISO7142CC-Q1.

Table 2. Function Table⁽¹⁾

V _{CCI}	V _{CCO}	INPUT (IN _x)	OUTPUT ENABLE (EN _x)	OUTPUT (OUT _x)
PU	PU	H	H or open	H
		L	H or open	L
		X	L	Z
		Open	H or open	H
PD	PU	X	H or open	H
PD	PU	X	L	Z
X	PD	X	X	Undetermined

(1) V_{CCI} = Input-side Supply Voltage; V_{CCO} = Output-side Supply Voltage; PU = Powered Up (V_{CC} ≥ 2.7 V); PD = Powered Down (V_{CC} ≤ 2.1 V); X = Irrelevant; H = High Level; L = Low Level; Z = High Impedance

8.4.1 Device I/O Schematics

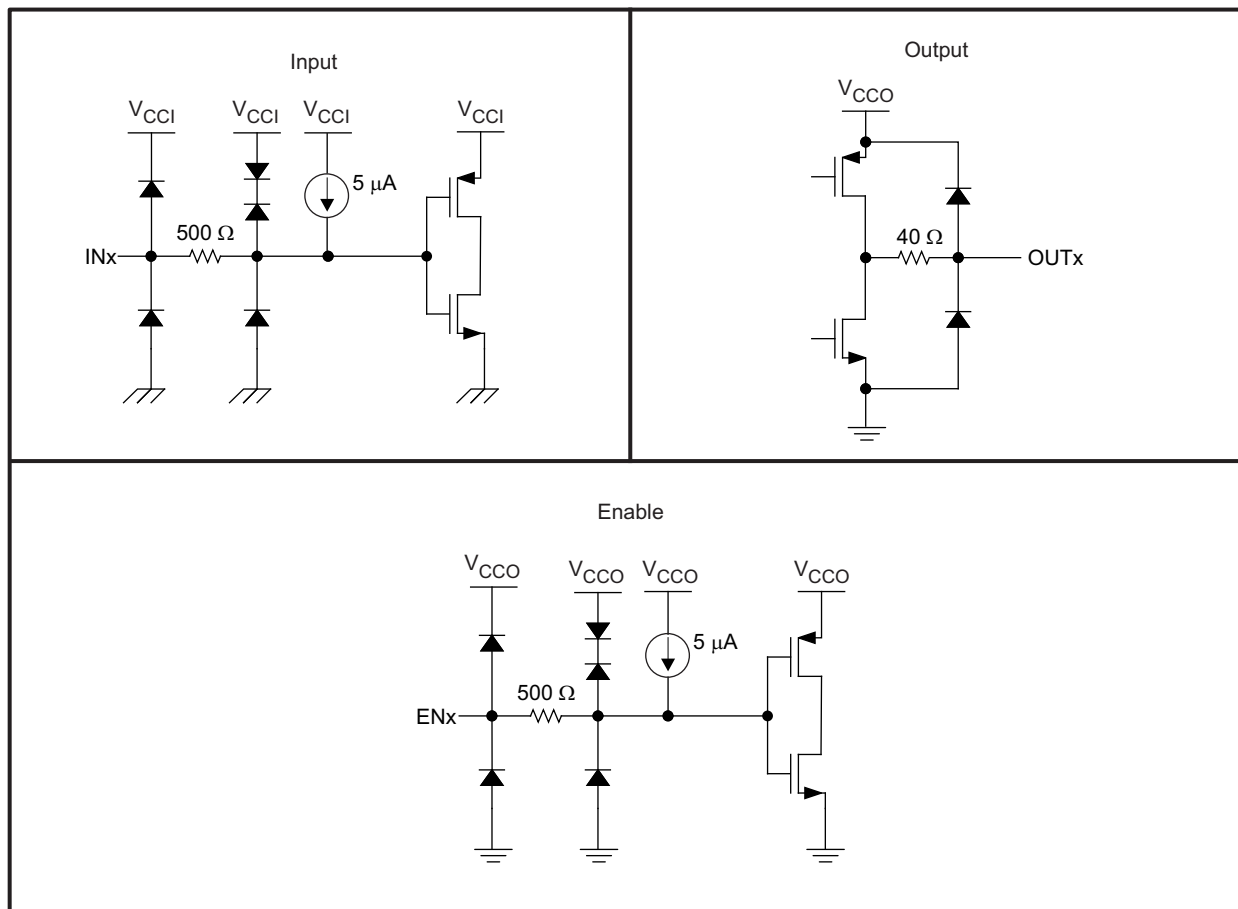


Figure 14. Device I/O Schematics

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The ISO7142CC-Q1 device uses single-ended TTL-logic switching technology. The supply voltage range is from 2.7 V to 5.5 V for both supplies, V_{CC1} and V_{CC2} . When designing with digital isolators, keep in mind that because of the single-ended design structure the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is, μC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

Figure 15 shows the typical isolated CAN interface implementation.

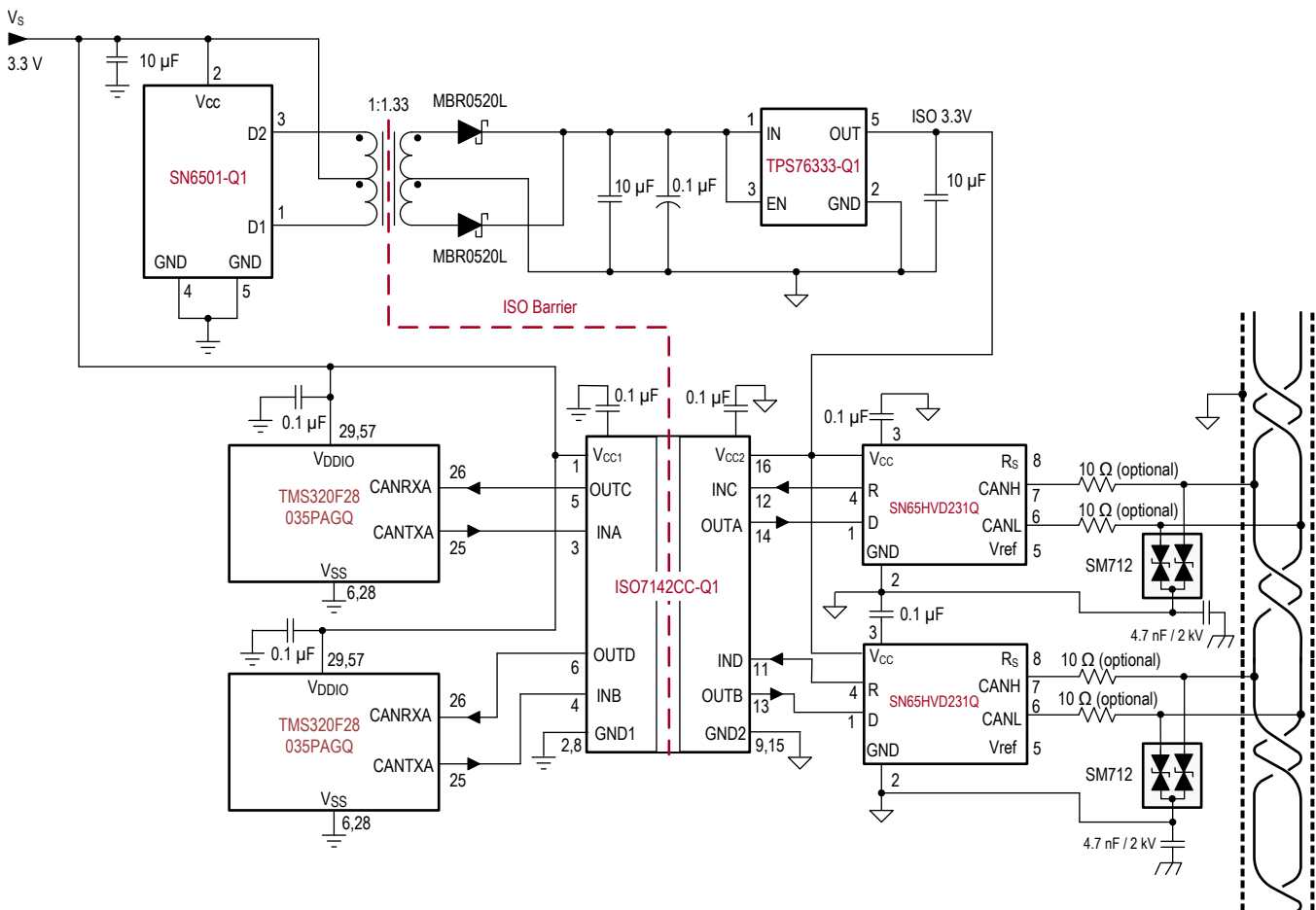


Figure 15. Typical Isolated CAN Application Circuit for ISO7142CC-Q1

9.2.1 Design Requirements

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO7142CC-Q1 device only requires two external bypass capacitors to operate.

Typical Application (continued)

9.2.2 Detailed Design Procedure

Figure 16 shows the hookup of a typical ISO7142CC-Q1 circuit. The only external components are two bypass capacitors.

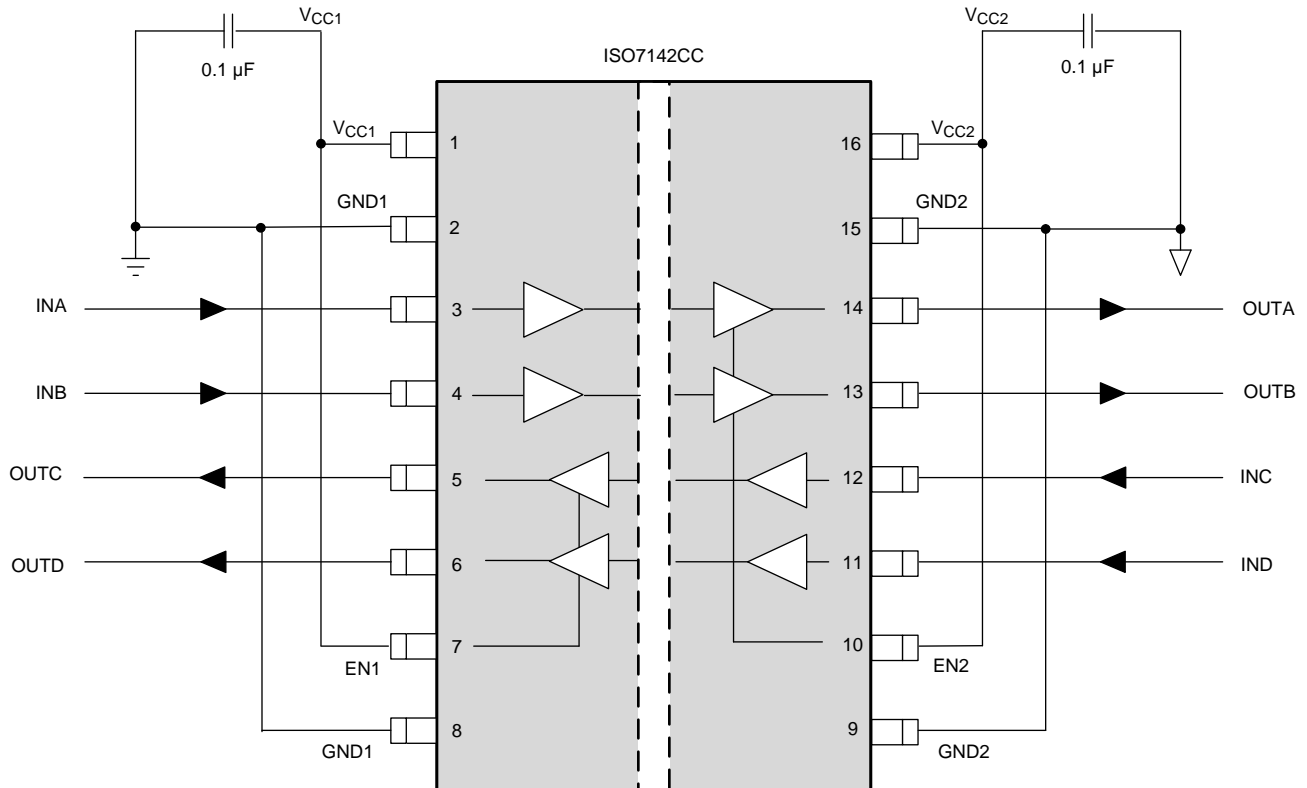


Figure 16. Typical ISO7142CC-Q1 Circuit Hook-up

9.2.3 Application Curves

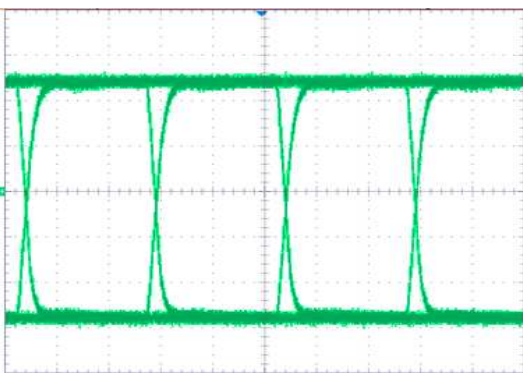


Figure 17. Typical Eye Diagram at 40 Mbps, PRBS 2¹⁶ - 1, 2.7-V Operation

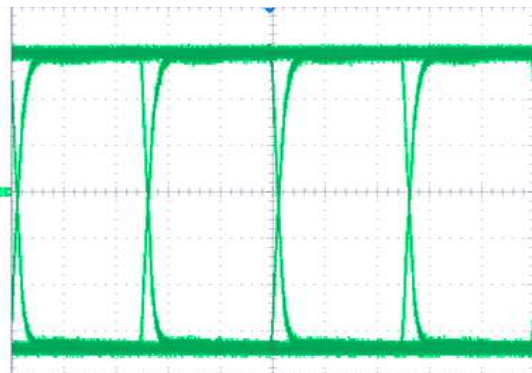


Figure 18. Typical Eye Diagram at 40 Mbps, PRBS 2¹⁶ - 1, 3.3-V Operation

Typical Application (continued)

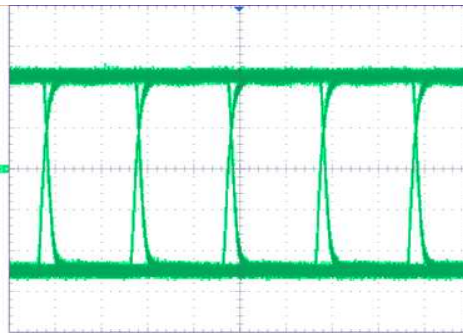


Figure 19. Typical Eye Diagram at 50 Mbps,
PRBS $2^{16} - 1$, 5-V Operation

10 Power Supply Recommendations

To help ensure reliable operation supply voltages, a 0.1- μF bypass capacitor is recommended at the input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' [SN6501-Q1](#). For such applications, detailed power supply design and transformer selection recommendations are available in SN6501-Q1 datasheet ([SLLSEF3](#)).

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 20](#)). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power and ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see the application note, *Digital Isolator Design Guide*, [SLLA284](#).

Layout Guidelines (continued)

11.1.1 PCB Material

For digital circuit boards operating below 150 Mbps, (or rise and fall times higher than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL 94 V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and self-extinguishing flammability-characteristics.

11.2 Layout Example

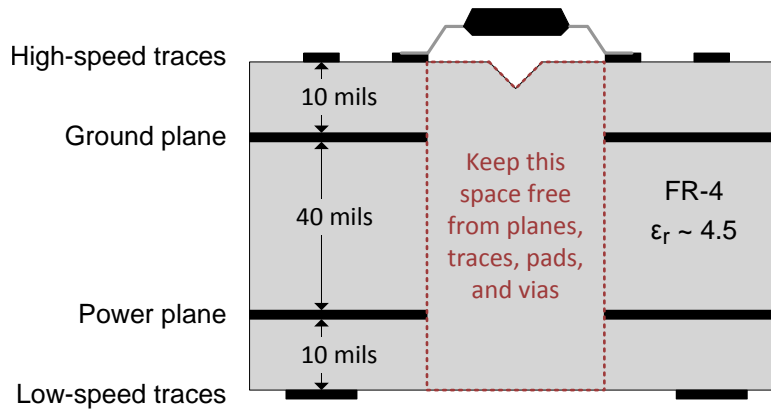


Figure 20. Recommended Layer Stack

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

相关文档如下:

- 《数字隔离器设计指南》， [SLLA284](#)
- 《隔离相关术语》， [SLLA353](#)
- 《ISO71xx EVM 用户指南》， [SLLU179](#)
- 《SN6501-Q1 用于隔离电源的变压器驱动器》， [SLLSEF3](#)
- 《SN65HVD231Q-Q1 3.3V CAN 收发器》， [SGLS398](#)
- 《TMS320F28035 *Piccolo™* 微控制器》， [SPRS584](#)
- 《TPS76333-Q1 低功耗 150mA 低压降线性稳压器》， [SGLS247](#)

12.2 社区资源

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12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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DLP® 产品	www.dlp.com	能源	www.ti.com.cn/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
时钟和计时器	www.ti.com.cn/clockandtimers	医疗电子	www.ti.com.cn/medical
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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7142CCQDBQQ1	ACTIVE	SSOP	DBQ	16	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7142Q	Samples
ISO7142CCQDBQRQ1	ACTIVE	SSOP	DBQ	16	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	7142Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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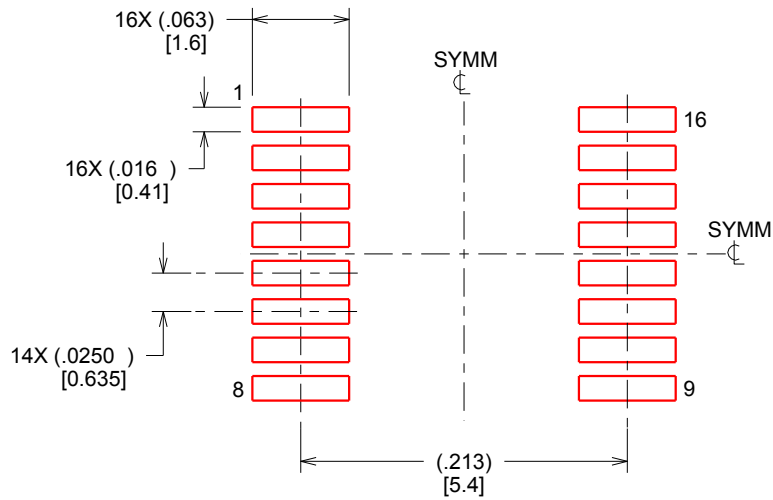
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EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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